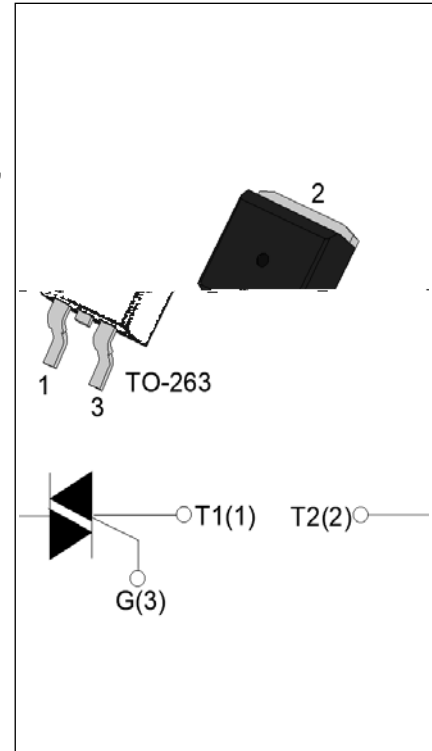




T1635H-8E 16A TRIAC

Rev.A.1.0

The T1635H-8E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T1635H-8E provides a very high switching capability up to junction temperatures of 150°C. Package TO-263 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	800	V
RMS on-state current ($T_c = 125^\circ\text{C}$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	160	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		176	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	128	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				70	
I_H	$I_T=500mA$		MAX.	35	mA
dV/dt	$V_D=540V$ Gate Open $T_j=150$		MIN.	1200	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , $T_j=150$		MIN.	15	A/ms
t_{on}	$I_G=40mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	8	μs
t_{off}				60	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.75	V
R_D	Dynamic resistance	$T_j=150$	27	m
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	2	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	W
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2cm^2$)	45	W

FIG.1 Maximum power dissipation versus RMS on-state current

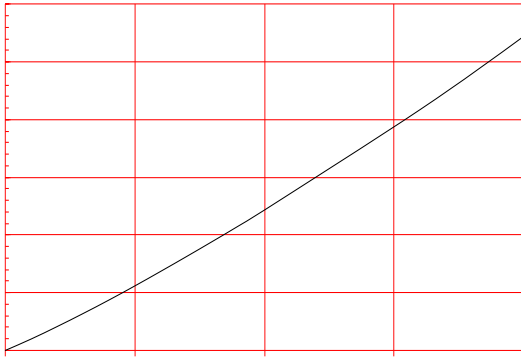


FIG.2: RMS on-state current versus case temperature

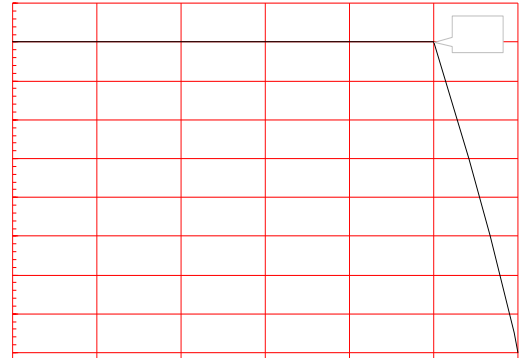


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)

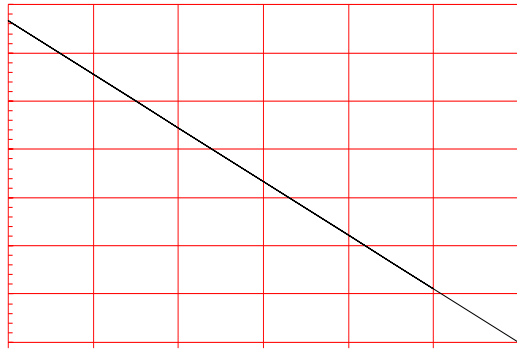


FIG.4: Surge peak on-state current versus number of cycles

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

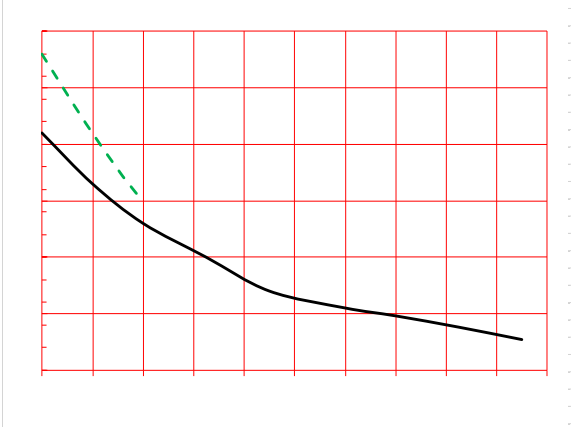
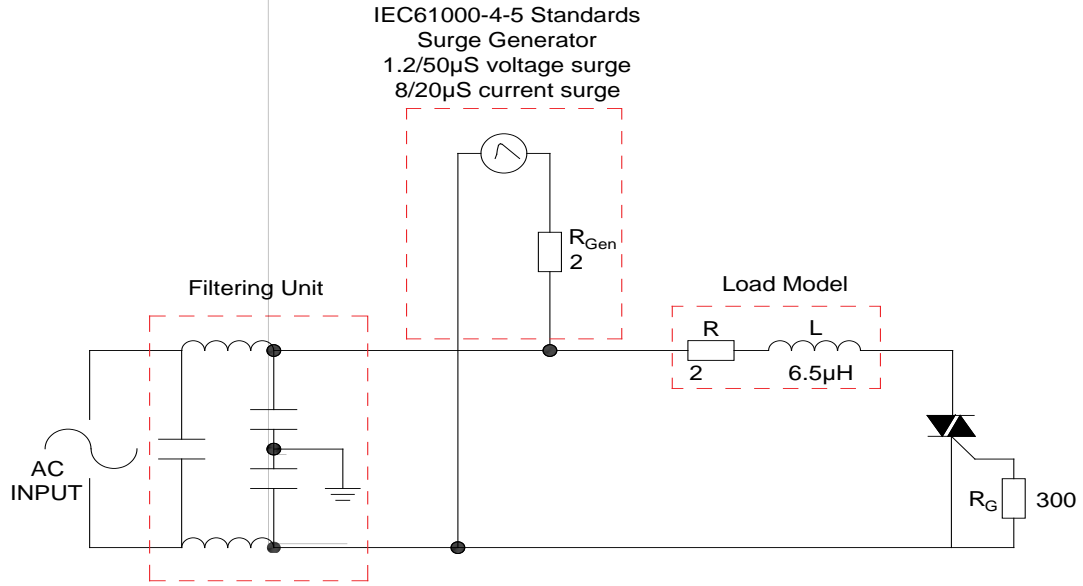


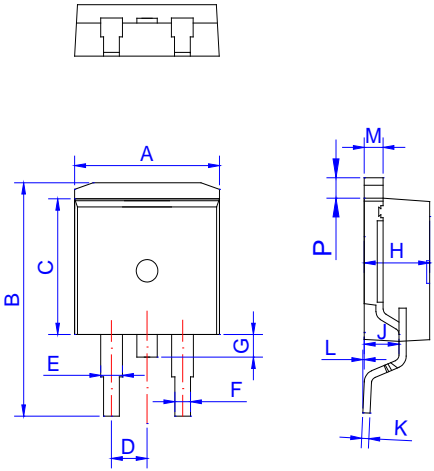
FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



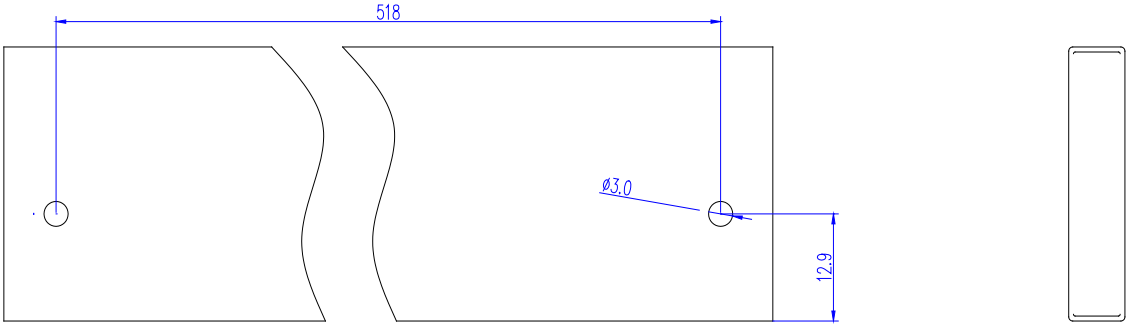
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T1635H-8E	800	35	TO-263	50	Tube
T1635H-8E-TR				800	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.37		0.378
D	2.40		2.70	0.094		0.106
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033
G	1.00		1.50	0.039		0.059
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053
P	1.20		1.50	0.047		0.059



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